



DESCRIPTION

AM3483 is available in a SOT-26 package.

ORDERING INFORMATION

Package Type	Part Number	
SOT-26	E6	AM3483E6R
		AM3483E6VR
Note	V: Halogen free Package R: Tape & Reel	
AiT provides all RoHS products Suffix “ V “ means Halogen free Package		

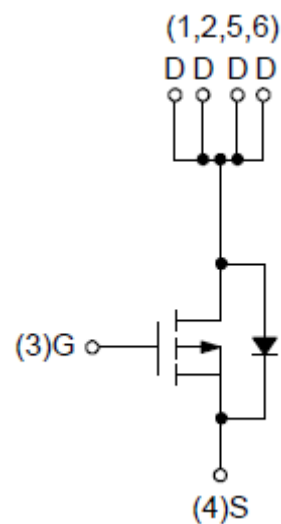
FEATURES

- -30V/-7.5V,
 $R_{DS(ON)} = 30m\Omega(max.) @ V_{GS} = -10V$
 $R_{DS(ON)} = 45m\Omega(max.) @ V_{GS} = -4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Available in a SOT-26 package.

APPLICATION

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

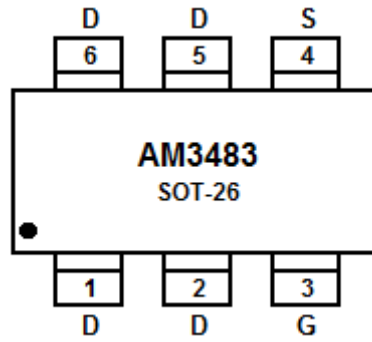
PIN DESCRIPTION



P-Channel MOSFET



PIN DESCRIPTION



Top View

Pin #	Symbol	Function
1,2,5,6	D	Drain
3	G	Gate
4	S	Source



ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted

V _{DSS} , Drain-Source Voltage		-30V
V _{GSS} , Gate-Source Voltage		±20V
I _D ^{NOTE1} , Continuous Drain Current (V _{GS} =-10V)	T _A =25°C	-7.5A
	T _A =70°C	-6A
I _{DM} ^{NOTE1} , 300µs Pulsed Drain Current (V _{GS} =-10V)		-30A
I _S ^{NOTE1} , Diode Continuous Forward Current		-2A
I _{AS} ^{NOTE2} , Avalanche Current, Single pulse (L=0.3mH)		-16A
E _{AS} ^{NOTE2} , Avalanche Energy, Single pulse (L=0.3mH)		38mJ
T _J , Maximum Junction Temperature		150°C
T _{STG} , Storage Temperature Range		-55°C~150°C
P _D ^{NOTE1} , Maximum Power Dissipation	T _A =25°C	2.5W
	T _A =70°C	1.6W
R _{θJA} ^{NOTE1} , Thermal Resistance-Junction to Ambient	t ≤ 10s	50°C/W
	Steady state	80°C/W

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Surface Mounted on 1in² pad area, t ≤ 10sec

NOTE2: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J=25°C).



ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless Otherwise Noted

Parameter	Symbol	Conditions	Min	Typ.	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
		T _J =85°C			-30	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =-250μA	-1.3	-1.8	-2.3	V
Gate Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Drain-Source On-state Resistance	R _{DS(ON)}	V _{GS} =-10V, I _{DS} =-7.5A	-	24	30	mΩ
	NOTE3	V _{GS} =-4.5V, I _{DS} =-4A	-	33	45	
Diode Characteristics						
Diode Forward Voltage	V _{SD} NOTE3	I _{SD} =-2A, V _{GS} =0V	-	-0.7	-1	V
Reverse Recovery Time	t _{rr} NOTE4	I _{SD} =-7.5A,	-	19	-	ns
Reverse Recovery Charge	Q _{rr} NOTE4	disD/dt=100A/μs	-	9	-	nC
Dynamic Characteristics NOTE4						
Gate Resistance	R _G	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	7	-	Ω
Input Capacitance	C _{ISS}	V _{GS} =0V,	-	840	-	pF
Output Capacitance	C _{OSS}	V _{DS} =-15V,	-	150	-	
Reverse Transfer Capacitance	C _{RSS}	Frequency=1.0MHz	-	110	-	
Turn-on Delay Time	t _{D(ON)}	V _{DD} =-15V, R _L =15Ω I _{DS} =-1A, V _{GEN} =-10V, R _G =6Ω	-	7.5	-	ns
Turn-on Rise Time	t _R		-	8	-	
Turn-off Delay Time	t _{D(OFF)}		-	37	-	
Turn-off Fall Time	t _F		-	16	-	
Gate Charge Characteristics NOTE4						
Total Gate Charge	Q _G	V _{DS} =-15V, V _{GS} =-10V, I _{DS} =-7.5A	-	18	-	nC
Gate-Source Charge	Q _{GS}		-	3	-	
Gate-Drain Charge	Q _{GD}		-	4	-	

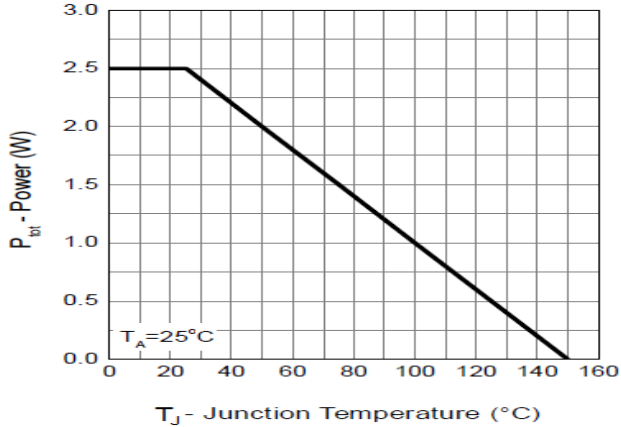
NOTE3: Pulse test; pulse width≤300μs, duty cycle≤2%.

NOTE4: Guaranteed by design, not subject to production testing.

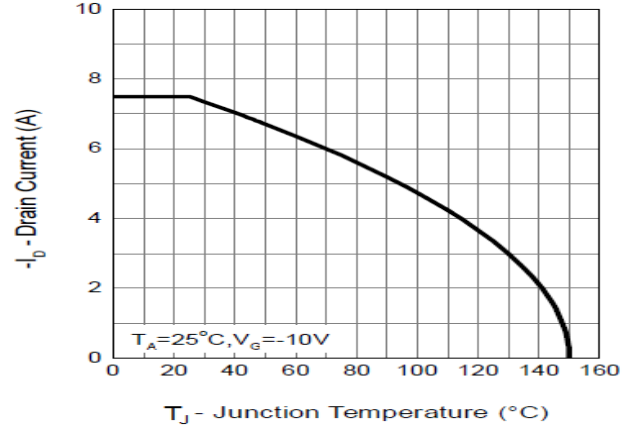


TYPICAL CHARACTERISTICS

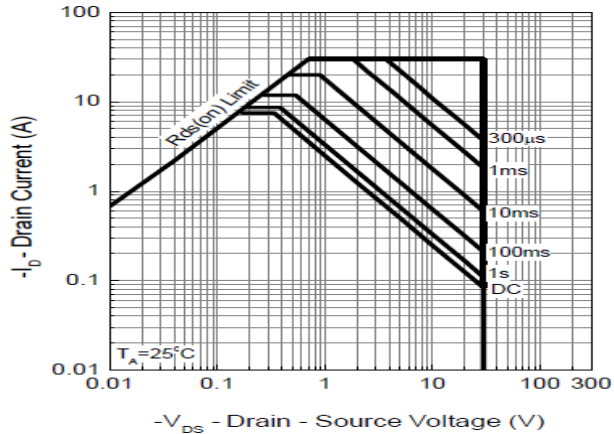
1. Power Dissipation



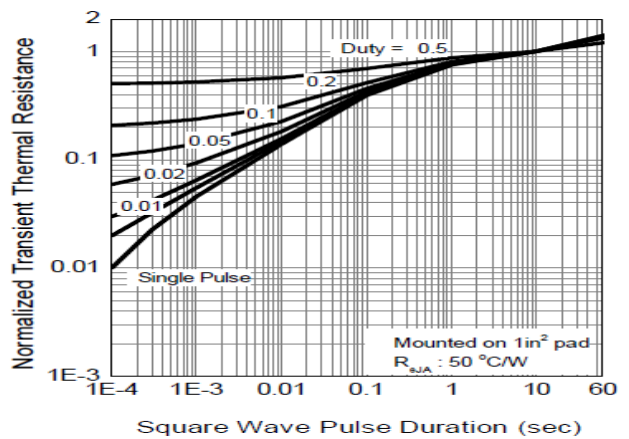
2. Drain Current



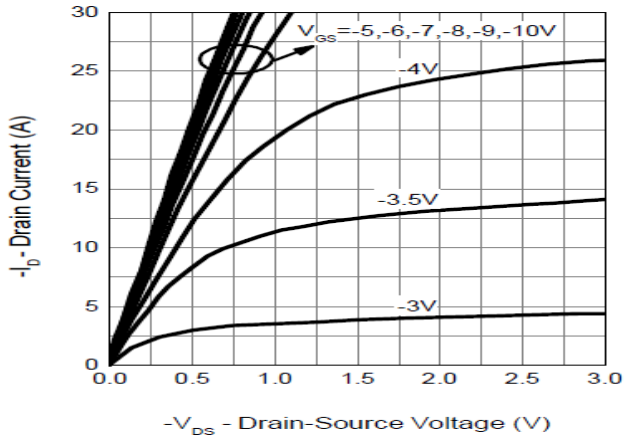
3. Safe Operation Area



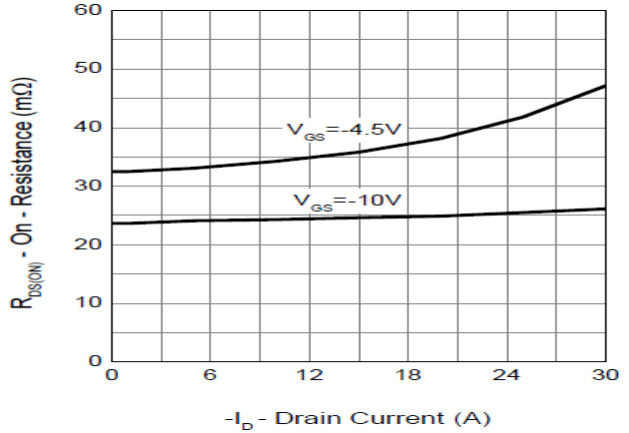
4. Thermal Transient Impedance



5. Output Characteristics

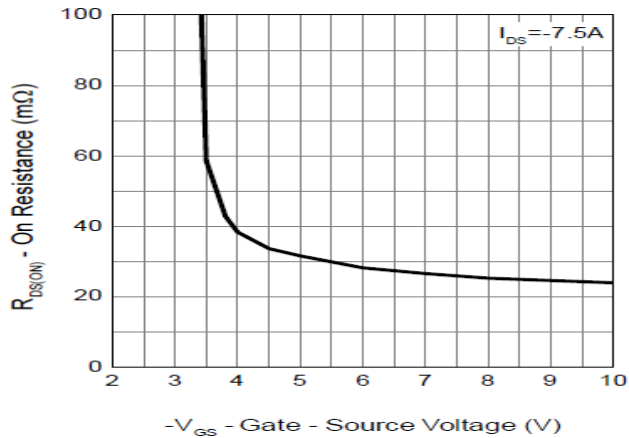


6. Drain-Source On Resistance

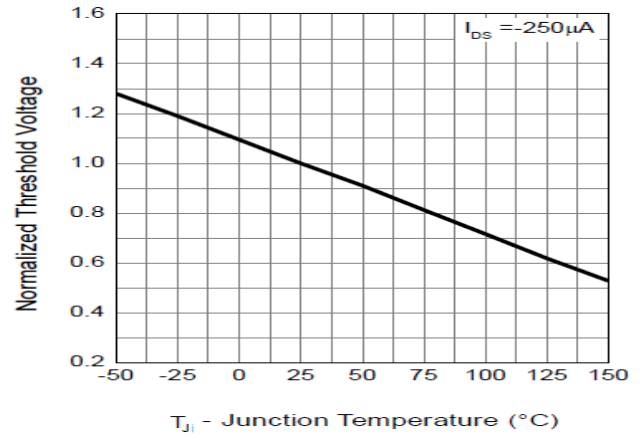




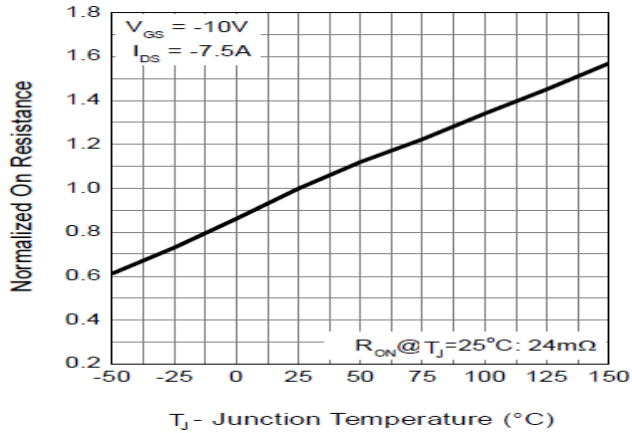
7. Gate-Source On Resistance



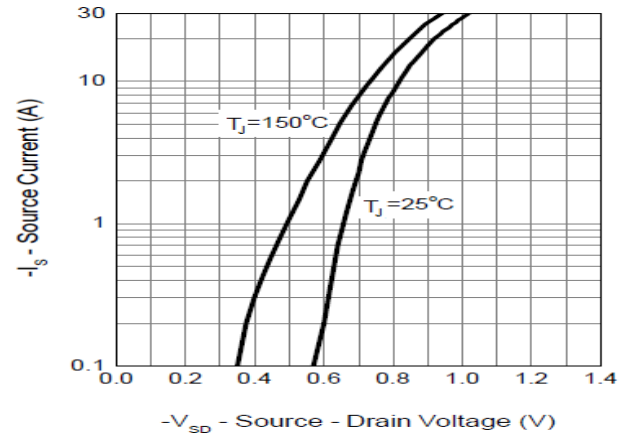
8. Gate Threshold Voltage



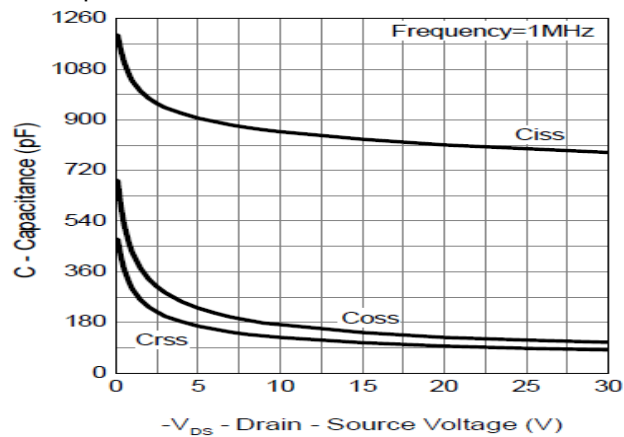
9. Drain-Source On Resistance



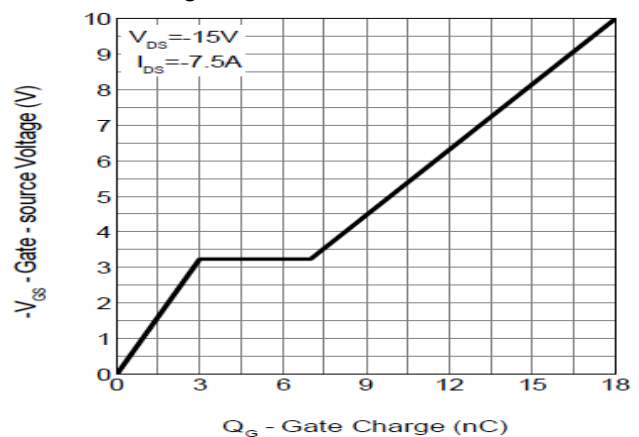
10. Source-Drain Diode Forward



11. Capacitance



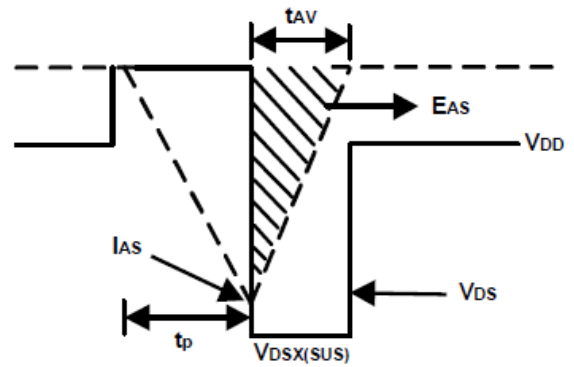
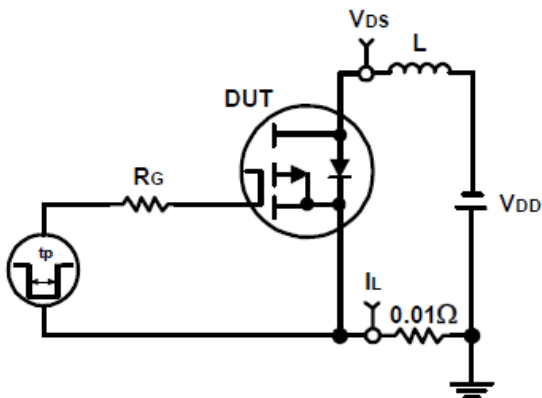
12. Gate Charge



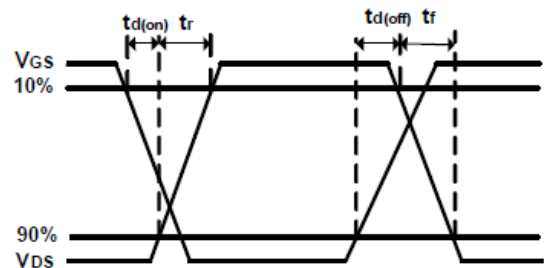
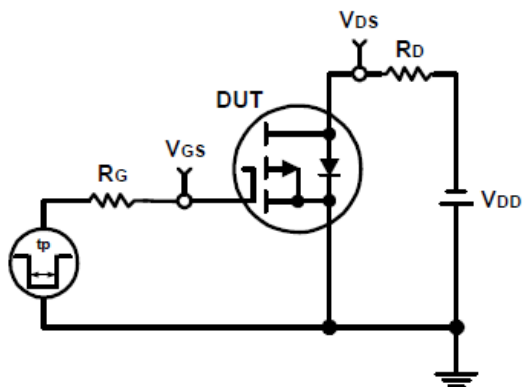


DETAILED INFORMATION

Avalanche Test Circuit and Waveforms



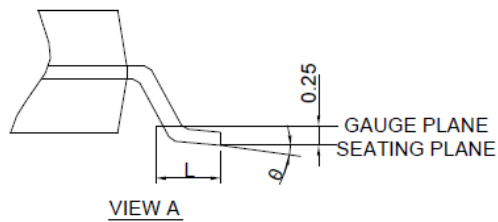
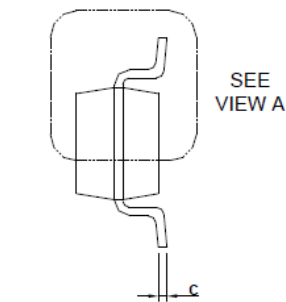
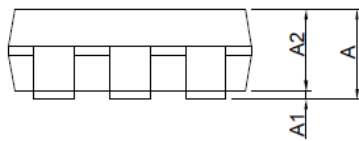
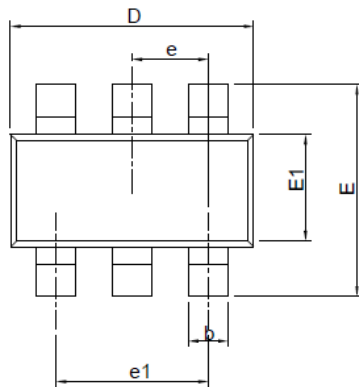
Switching Time Test Circuit and Waveforms



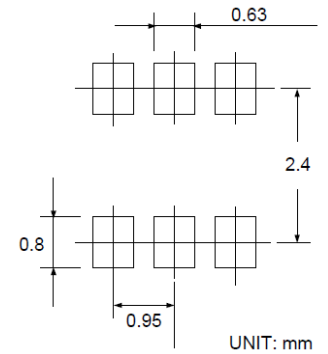


PACKAGE INFORMATION

Dimension in SOT-26 Package (Unit: mm)



RECOMMENDED LAND PATTERN



SYMBOL	MIN	MAX
A	-	1.250
A1	0.000	0.150
A2	0.900	1.300
b	0.300	0.500
c	0.080	0.220
D	2.700	3.100
E	1.400	1.800
E1	2.600	3.000
e	0.950(BSC)	
e1	1.900(BSC)	
L	0.300	0.600
θ	0°	8°



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